

isc N-Channel MOSFET Transistor

IRFZ44N, IIRFZ44N

• FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤17.5mΩ
- · Enhancement mode
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



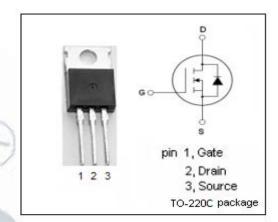
· reliable device for use in a wide variety of applications

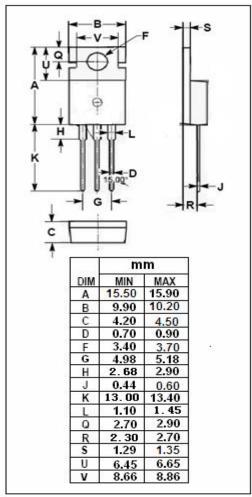


SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	55	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	49	A	
I _{DM}	Drain Current-Single Pulsed	ulsed 160		
P _D	Total Dissipation @T _C =25℃	94	W	
Tj	Max. Operating Junction Temperature	175	$^{\circ}$ C	
T _{stg}	Storage Temperature	-55~175	°C	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1.5	°C/W
Rth(ch-a)	th(ch-a) Channel-to-ambient thermal resistance		°C/W







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ELECTRICAL CHARACTERISTICS

 T_{C} =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	55			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =25A			17.5	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V			±0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =55V; V _{GS} = 0V			25	μ А
V _{SD}	Diode forward voltage	Is=25A, V _{GS} = 0 V			1.3	V

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